NSN 5961-01-212-8019

Thyristor Semiconductor Device - Page 1 of 2

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Inclosure Material:

Metal

Overall Length:

Between 0.240 inches and 0.260 inches

Terminal Length:

Between 0.500 inches and 0.750 inches

Overall Diameter:

Between 0.335 inches and 0.370 inches

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-5

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Terminal

Terminal Circle Diameter:

0.200 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

2.2 forward voltage, peak and 200.0 reverse voltage, peak and 300.0 nonrepetitive peak reverse voltage, peak total value

Current Rating Per Characteristic:

0.22 amperes forward current, average absolute and 15.00 amperes forward current, average preset

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: pnpn

Precious Material And Location:

Terminal surface option gold

Precious Material:

Gold

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

3 uninsulated wire lead

Specification Data:

81349-mil-s-19500/276 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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